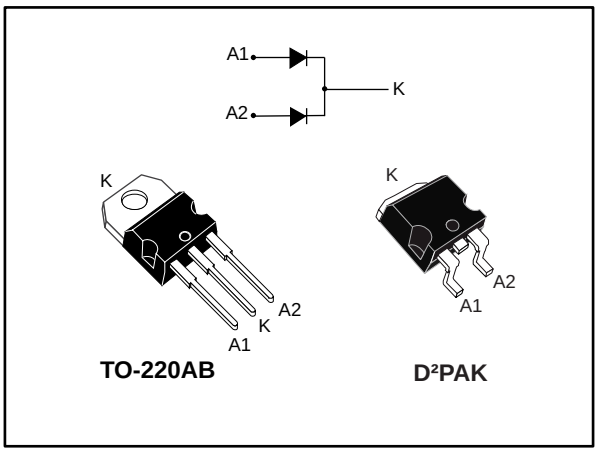
FERD40L60C

60 V field-effect rectifier diode

Datasheet - production data



Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Reduced leakage current
- Low forward voltage drop
- High frequency operation

Description

The device is based on a proprietary technology that achieves the best in class V_F/I_R trade-off for a given silicon surface.

This 60 V rectifier has been optimized for use in confined applications where both efficiency and thermal performance are key.

This device is suitable for use in adapters and chargers.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	2 x 20 A
V_{RRM}	60 V
V_F (typ.)	0.375 V
T_j (max.)	150 °C

This is information on a product in full production.

www.st.com

1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, per diode, unless otherwise specified)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			60	V
$I_{F(RMS)}$	Forward rms current			60	A
$I_{F(AV)}$	Average forward current δ = 0.5, square wave	T_C = 130 °C	Per diode	20	A
			Per device	40	
I_{FSM}	Surge non repetitive forward current	t_p = 10 ms sinusoidal		250	A
T_{stg}	Storage temperature range			-65 to +175	°C
T_j	Maximum operating junction temperature (1)			+150	°C

Notes:

(1)$(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal resistance parameters

Symbol	Parameter		Max. value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.3	°C/W
		Per device	0.8	
$R_{th(c)}$	Coupling		0.3	

Table 4: Static electrical characteristics, per diode

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I_R(1)	Reverse leakage current	T_j = 25 °C	$V_R = V_{RRM}$	-		1.1	mA
		T_j = 125 °C		-	40	80	
		T_j = 125 °C	V_R = 45 V	-	23	46	
V_F(2)	Forward voltage drop	T_j = 25 °C	I_F = 4 A	-	0.32	0.36	V
		T_j = 125 °C		-	0.26	0.3	
		T_j = 25 °C	I_F = 10 A	-	0.4	0.445	
		T_j = 125 °C		-	0.375	0.425	
		T_j = 25 °C	I_F = 20 A	-	0.49	0.545	
		T_j = 125 °C		-	0.515	0.58	

Notes:

(1)Pulse test: t_p = 5 ms, δ < 2%

(2)Pulse test: t_p = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:

$P = 0.27 \times I_{F(AV)} + 0.0155 \times I_{F^2(RMS)}$

1.1 Characteristics (curves)

Figure 1: Average forward current versus ambient temperature (δ = 0.5, per diode)

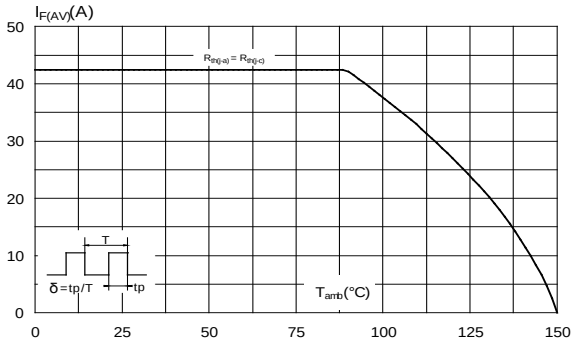


Figure 2: Relative variation of thermal impedance junction to case versus pulse duration

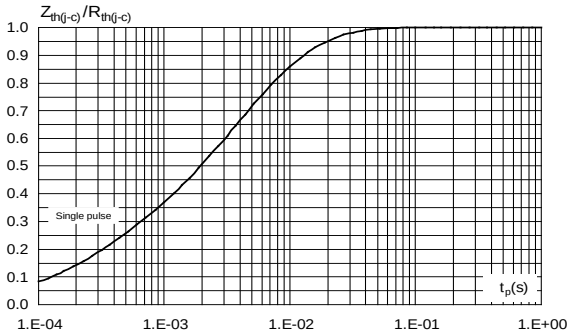


Figure 3: Reverse leakage current versus reverse voltage applied (typical values, per diode)

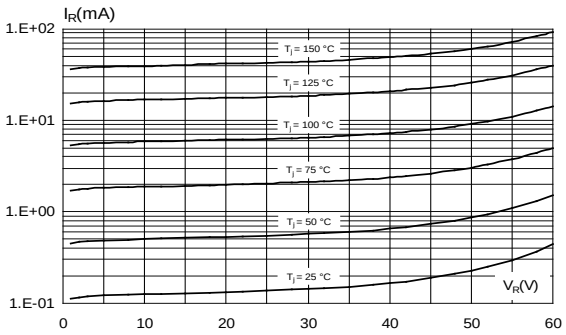


Figure 4: Junction capacitance versus reverse voltage applied (typical values, per diode)

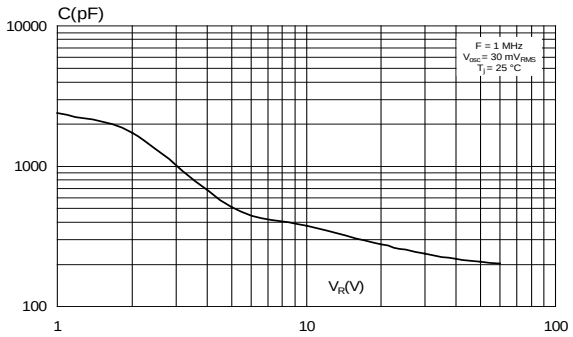


Figure 5: Forward voltage drop versus forward current (typical values, per diode)

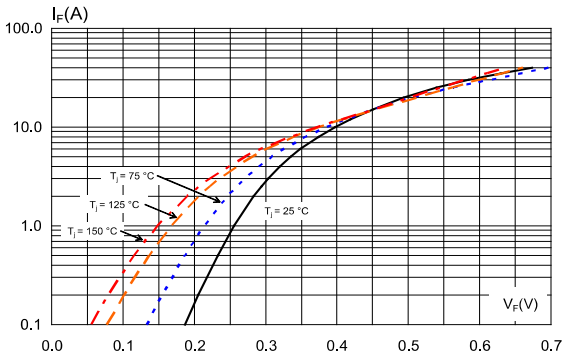


Figure 6: Forward voltage drop versus forward current (typical values, per diode)

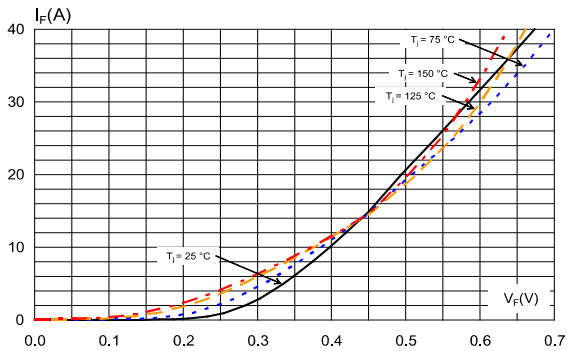
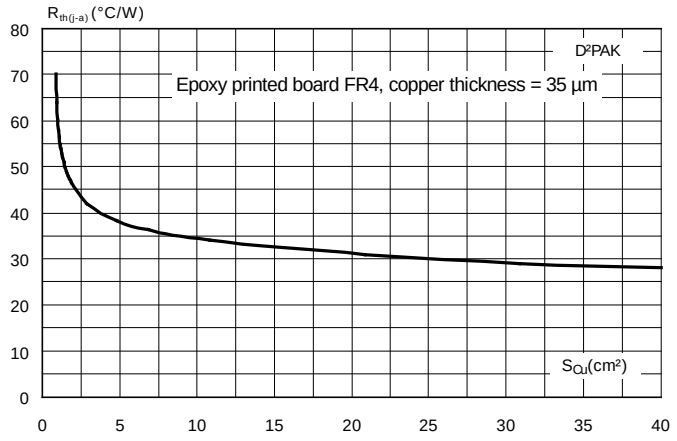


Figure 7: Thermal resistance junction to ambient versus copper surface under tab for D²PAK (typical values)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL94,V0
- Recommended torque value: 0.55 N·m (for TO-220AB)
- Maximum torque value: 0.6 N·m (for TO-220AB)

2.1 TO-220AB package information

Figure 8: TO-220AB package outline

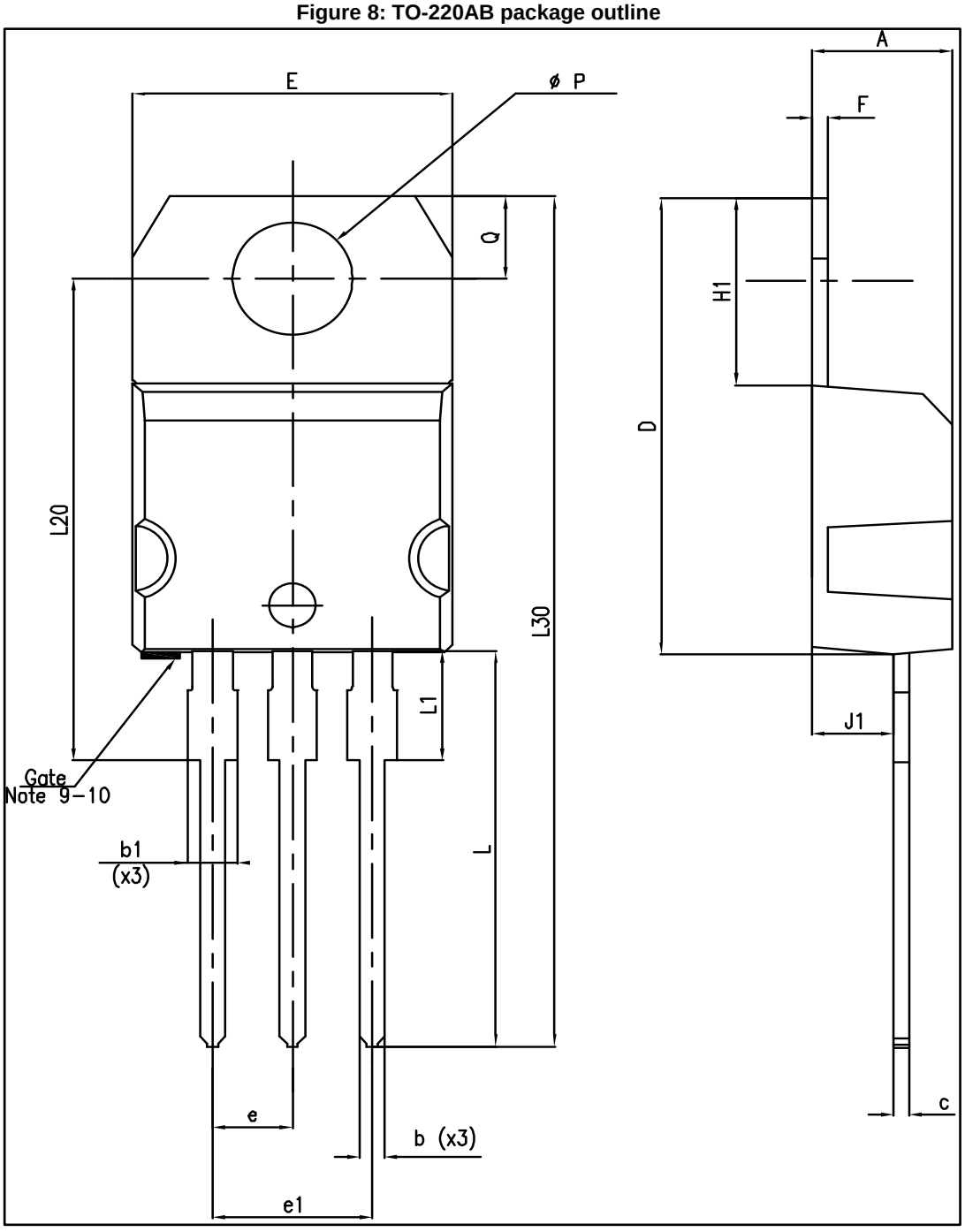


Table 5: TO-220AB package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.045	0.067
c	0.48	0.70	0.019	0.028
D	15.25	15.75	0.600	0.620
E	10.00	10.40	0.394	0.409
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
F	0.51	0.60	0.020	0.024
J1	2.40	2.72	0.094	0.107
H1	6.20	6.60	0.244	0.256
L	13.00	14.00	0.512	0.551
L1	3.50	3.93	0.138	0.155
L20	16.40 typ.		0.646 typ.	
L30	28.90 typ.		1.138	
Ø P	3.75	3.85	0.148	0.156
Q	2.65	2.95	0.104	0.116

2.2 D²PAK package information

Figure 9: D²PAK package outline

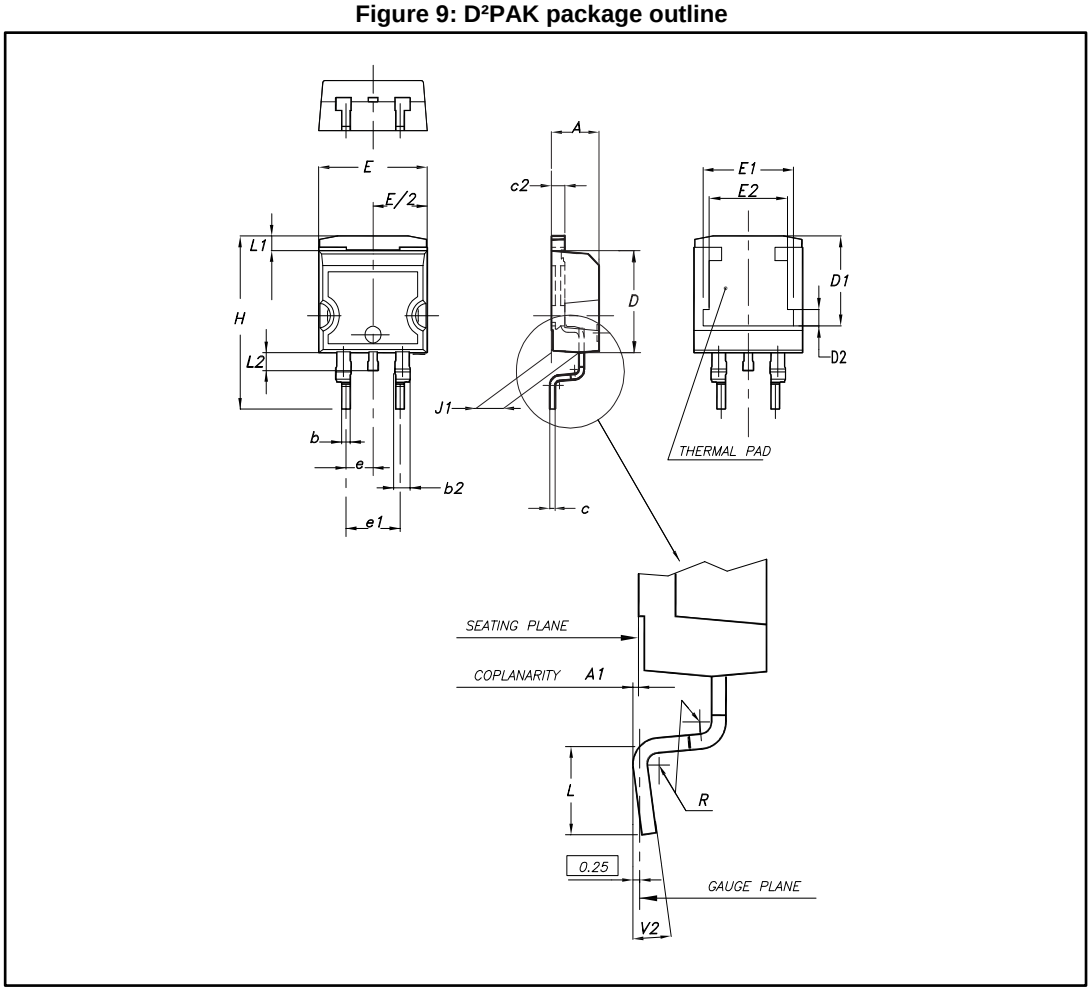
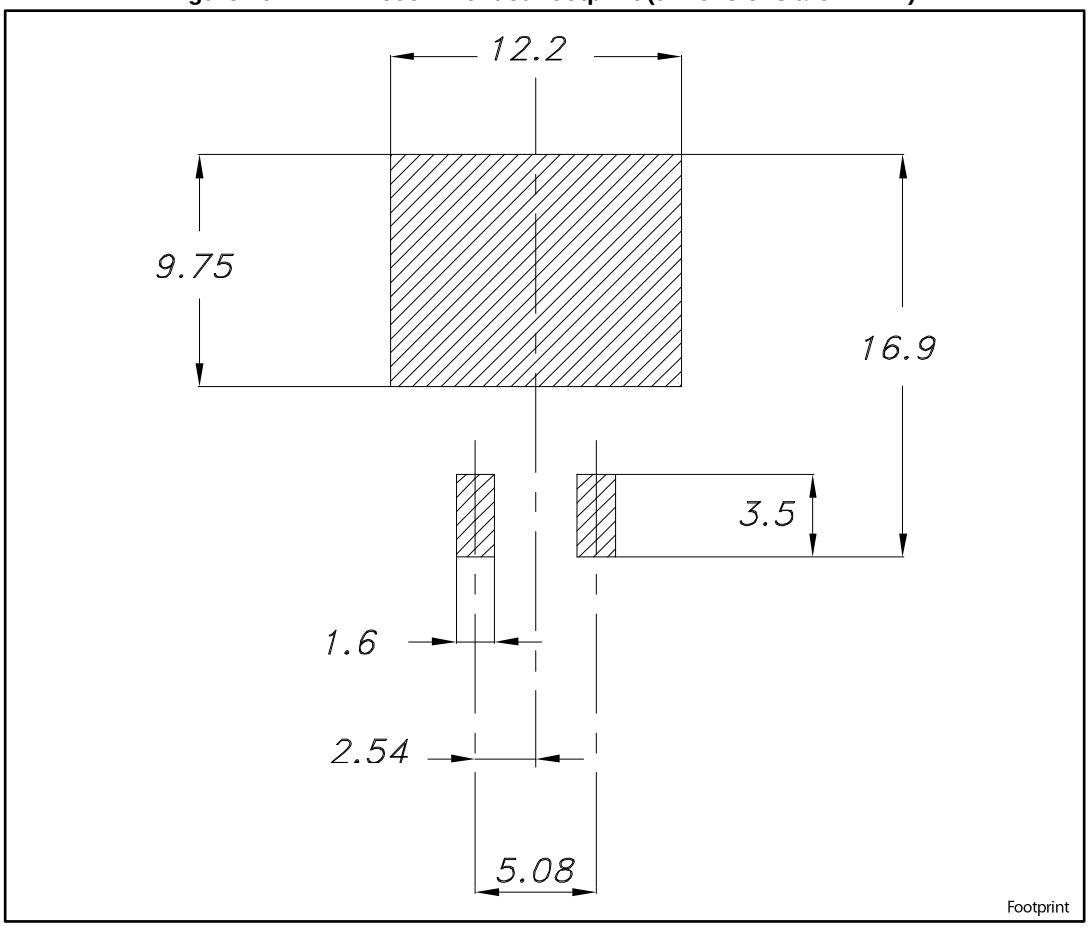


Table 6: D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409
E1	8.50	8.70	8.90	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

Figure 10: D²PAK recommended footprint (dimensions are in mm)



3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
FERD40L60CTS	FD40L60CTS	TO-220AB	1.38 g	50	Tube
FERD40L60CG-TR	FD40L60CG	D²PAK	1.43 g	1000	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
01-Sep-2017	1	Initial release.

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